



VCC-113A13H

1130nm 13mW Oxide VCSEL Emitter

Features

- 1130nm multi-emitter oxide VCSEL emitter
- Output power: 13mW
- Wide temperature operation

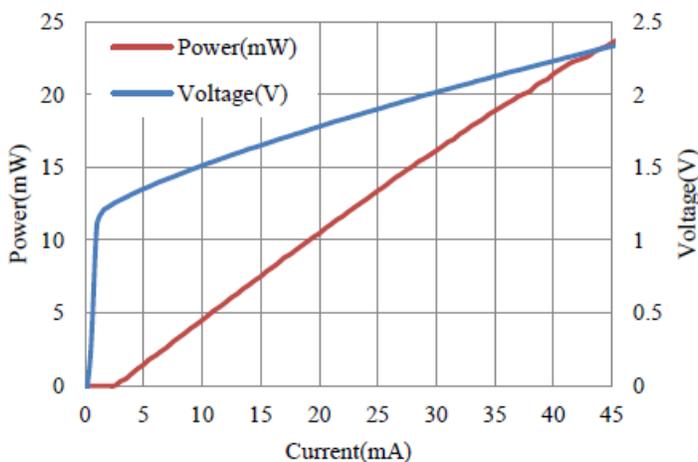
Specifications

Absolute Maximum Ratings				
Parameters	Min.	Max.	Unit	Conditions
Storage Temperature	-40	125	°C	
Operating Temperature	-40	85	°C	
Continuous Forward Current		30	mA	
Solder Reflow Temperature		260	°C	Max 10 seconds

Electro-Optical Characteristics (T _a =25°C unless otherwise stated)						
Parameters	Symbol	Min.	Typ.	Max.	Unit	Conditions
Threshold Current	I _{th}		3		mA	
Slope Efficiency	η		0.6		mW/mA	
Optical Output Power	P _o	10	13	16	mW	I _f =25mA
Wavelength	λ _P	1115	1130	1145	nm	I _f =25mA
Wavelength Shift	Δλ _P /ΔT		0.07		nm/°C	
Beam Divergence	Θ		23		°	I _f =25mA
Forward Voltage	V _f	1.7	1.9	2.1	V	I _f =25mA

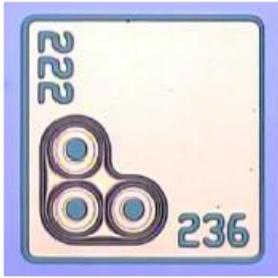
Notes: All parameters except mentioned are measured at 25°C, CW operation.

Typical Characteristic Curves



Typical electro / optical characteristics curves measured at 25°C, CW operation

Outline Dimensions



- Chip length: 160um +/- 15um
- Chip width: 160um +/- 15um
- Chip thickness: 100 +/- 15um
- Anode bond pad: Dia. 95um +/- 2um

Additional Notes

- The inherent design of this component causes it to be sensitive to electrostatic discharge (ESD). To prevent ESD-induced damage and/or degradation to equipment, take normal ESD precautions when handling this product.
- Specifications are subject to change without notice.